

Abstract Submitted
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Investigation of LaOx Removal for Application in CMOS Devices¹

KELLY RADER, Texas State University-San Marcos — Following Moore's Law, transistor devices continue to scale down and the use of silicon dioxide as the insulating oxide layer is no longer feasible due to gate leakage. Investigation into new "high-k materials" has become necessary. Research on LaOx will be presented with potential application in CMOS technology. Specifically, experimental results about LaOx wet etch development, a key step in CMOS processing, will be presented.

¹SEMATECH

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